Rev. 6 — 14 December 2011

Product data sheet

1. General description

The 74HC00; 74HCT00 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC00; 74HCT00 provides a quad 2-input NAND function.

2. Features and benefits

- Input levels:
 - For 74HC00: CMOS level
 - ◆ For 74HCT00: TTL level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3. Ordering information

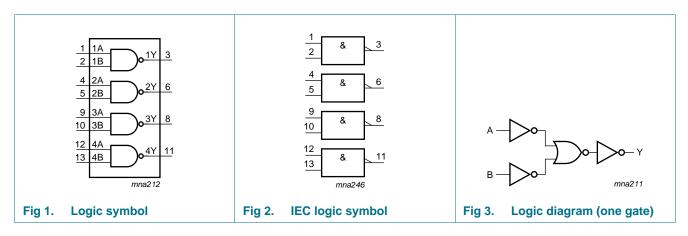
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC00N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT00N				
74HC00D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1
74HCT00D			3.9 mm	
74HC00DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1
74HCT00DB			width 5.3 mm	
74HC00PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1
74HCT00PW			body width 4.4 mm	
74HC00BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1
74HCT00BQ			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	



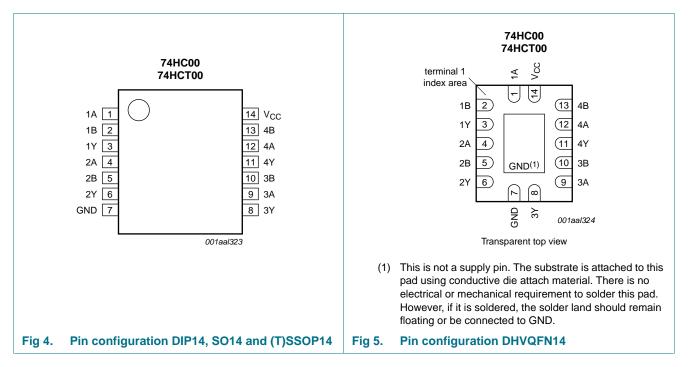
Quad 2-input NAND gate

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input

74HC_HCT00		
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74HC00; 74HCT00

Table 2.	Pin description contin	nued
Symbol	Pin	Description
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3.	Function table ^[1]		
Input			Output
nA		nB	nY
L		x	Н
Х		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V_{I} < -0.5 V or V_{I} > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
l _{ок}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2]		
	DIP14 package		-	750	mW
	SO14, (T)SSOP14 and DHVQFN14 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C. For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C. For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC0	74HC00			74HCT00		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		−40 °C 1	to +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC00										
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	-	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	-	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	-	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	-	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	-	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	-	-	1.8	-	1.8	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$								
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	-	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	4.5	-	4.4	-	4.4	-	V
		$I_0 = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	-	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 20 \ \mu A; V_{CC} = 2.0 \ V$	-	0	-	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	-	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	-	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	-	-	0.33	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	-	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	-	-	±1	-	±1	μA
lcc	supply current		-	-	-	-	20	-	40	μA

Quad 2-input NAND gate

Symbol	Parameter	Conditions		25 °C		−40 °C	–40 °C to +85 °C		–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	Min	Мах	
CI	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT0	0									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.6	-	2.0	-	2.0	-	V
VIL	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$								
	output voltage	I _O = -20 μA	-	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	-	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$								
	output voltage	$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	-	-	0.1	-	0.1	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.15	-	-	0.33	-	0.4	V
lı	input leakage current	$V_1 = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	-	-	±1	-	±1	μA
I _{CC}	supply current		-	-	-	-	20	-	40	μA
ΔI _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	150	-	-	675	-	735	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

10. Dynamic characteristics

Table 7.Dynamic characteristics

 $GND = 0 V; C_L = 50 pF;$ for load circuit see <u>Figure 7</u>.

Symbol	Parameter	r Conditions		25 °C			–40 °C to +125 °C		Unit
			Min	Тур	Мах	Max (85 °C)	Max (125 °C)		
74HC00									
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	25	-	115	135	ns
	$V_{CC} = 4.5 V$		-	9	-	23	27	ns	
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 V$		-	7	-	20	23	ns
t _t	transition time	see Figure 6	[2]						
		$V_{CC} = 2.0 V$		-	19	-	95	110	ns
		$V_{CC} = 4.5 V$		-	7	-	19	22	ns
		$V_{CC} = 6.0 V$		-	6	-	16	19	ns

Quad 2-input NAND gate

Symbol	Parameter	Conditions	Conditions		25 °C			–40 °C to +125 °C		
				Min	Тур	Max	Max (85 °C)	Max (125 °C)		
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	22	-	-	-	pF	
74HCT00)									
t _{pd}	propagation delay	nA, nB to nY; see <u>Figure 6</u>	<u>[1]</u>							
		$V_{CC} = 4.5 V$		-	12	-	24	29	ns	
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns	
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u>	[2]	-	-	-	29	22	ns	
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	22	-	-	-	pF	

Table 7. Dynamic characteristics ...continued GND = 0 V: $C_{i} = 50$ pE: for load circuit see Figure 7.

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

11. Waveforms

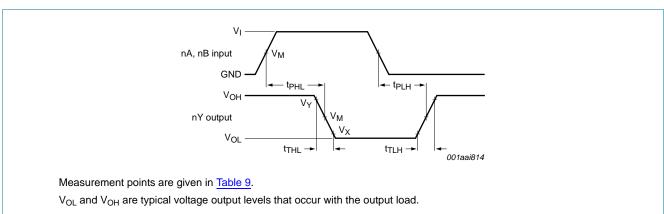


Fig 6. Input to output propagation delays

Table 8. Measurement points

Туре	Input	Output		
	V _M	V _M	V _X	V _Y
74HC00	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}
74HCT00	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}

74HC_HCT00
Product data sheet

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74HC00; 74HCT00

Quad 2-input NAND gate

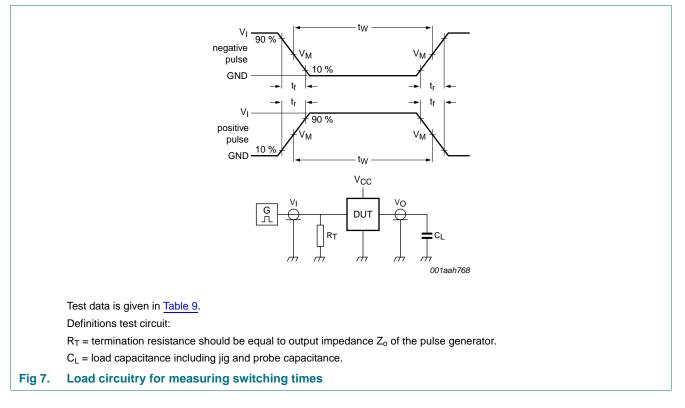


Table 9. Test data

Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74HC00	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT00	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

Quad 2-input NAND gate

12. Package outline

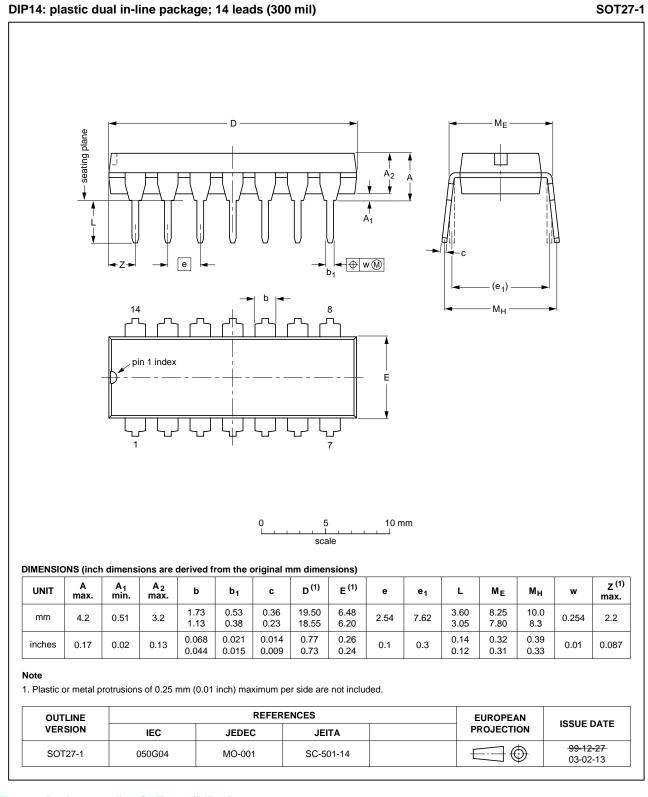
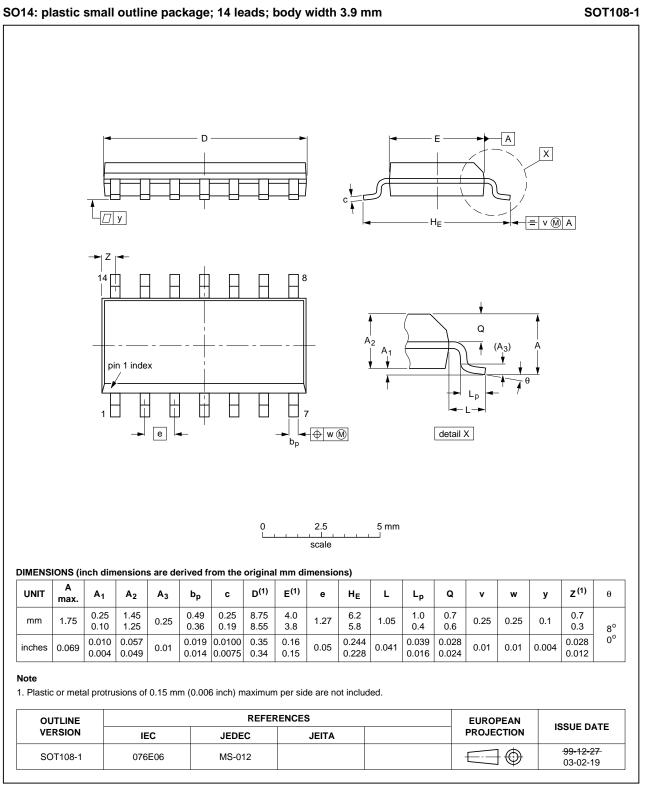


Fig 8. Package outline SOT27-1 (DIP14)

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Package outline SOT108-1 (SO14) Fig 9.

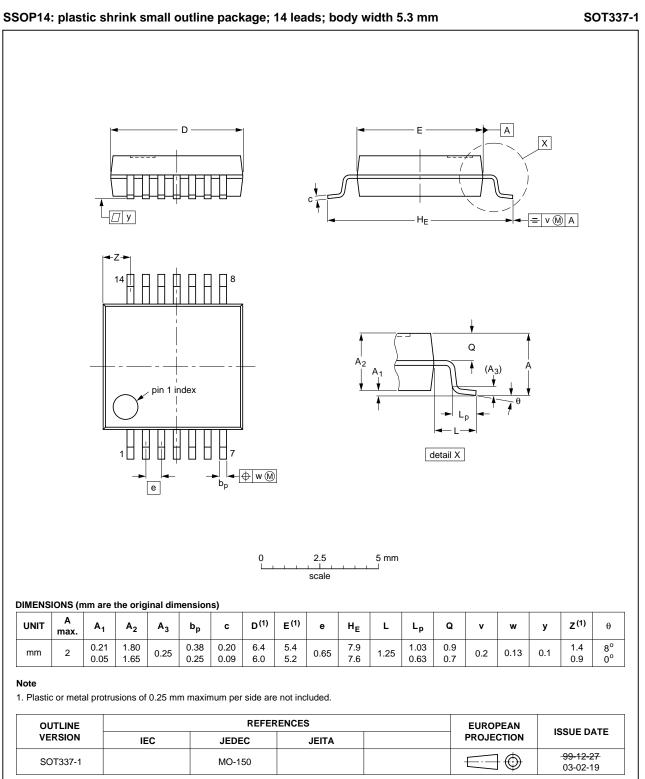


Fig 10. Package outline SOT337-1 (SSOP14)

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Quad 2-input NAND gate

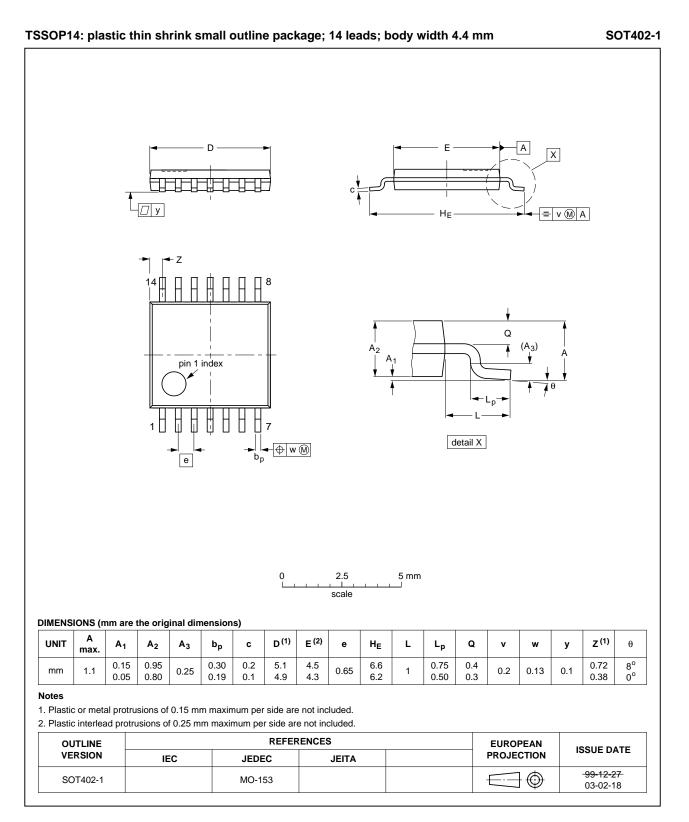
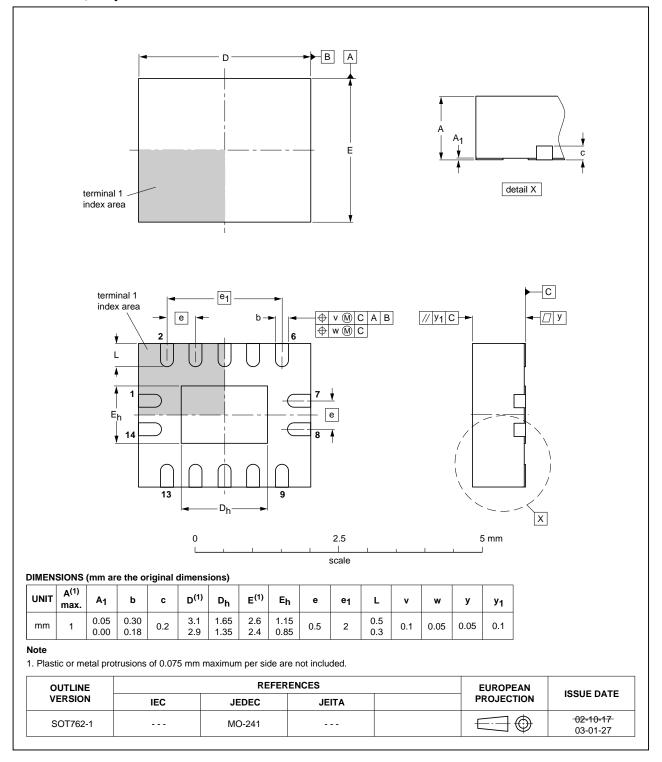


Fig 11. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 12. Package outline SOT762-1 (DHVQFN14)

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13. Abbreviations

Table 10. Abbreviations	
Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT00 v.6	20111214	Product data sheet	-	74HC_HCT00 v.5
Modifications:	 Legal pages update 	ed.		
74HC_HCT00 v.5	20101125	Product data sheet	-	74HC_HCT00 v.4
74HC_HCT00 v.4	20100111	Product data sheet	-	74HC_HCT00 v.3
74HC_HCT00 v.3	20030630	Product data sheet	-	74HC_HCT00_CNV v.2
74HC_HCT00_CNV v.2	19970826	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Quad 2-input NAND gate

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